风光欣技术资料

C3205

—NPN silicon —

■■**APPLICATION:** High Current Applications.

■■**MAXIMUM RATINGS**（Ta＝25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	30	V
Collector-emitter voltage	V_{CEO}	30	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	2	A
Collector Power Dissipation	P_C	1	W
Junction Temperature	T_J	150	℃
Storage Temperature Range	Tstg	－55~150	℃

TO-92L

1. Emitter 2. Collector 3. Base

■■**ELECTRICAL CHARACTERISTICS（Ta=25℃）**

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	100		320		V_{CE}= 2V，Ic= 500mA
Collector Cut-off Current	I_{CBO}			0.1	μA	V_{CB}= 30V，I_E=0
Emitter Cut-off Current	I_{EBO}			0.1	μA	V_{EB}= 5V，Ic=0
Collectoe-Base Breakdown Voltage	BV_{CBO}	30			V	Ic= 0.1mA，I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	30			V	Ic= 10mA，I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	5			V	I_E= 0.1mA，Ic=0
Base-Emitter Voltage	V_{BE}			1.0	V	V_{CE}= 2V，Ic= 500mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			2.0	V	Ic= 1.5A，I_B= 30mA
Gain bandwidth product	f_T		120		MHz	Ic= 500mA，V_{CE}= 2V
Common Base Output Capacitance	Cob		13		PF	V_{CB}= 10V，I_E=0，f =1MHz

■■hFE **Classification And Marking**

Classification	O	Y
h_{FE}	100～200	160～320